18. Semiconductor Doping by Ion Implantation

18.a. General and Reviews

Performance of a sputter ion source and its application for implanted ion profile experiments
G. Brown and M. L. Renton

Heavy ion-induced characteristic x-rays as a tool in solid state physics
J. A. Cairns

A technique for elucidating, with high sensitivity, the concentration profile of an ion-implanted element

Effects produced by ion bombardment and implantation into thin films and surfaces

Use of low-energy accelerators for ion implantation
P. J. Cracknell, M. Gettings, and K. G. Stephens

Use of compound semiconductors in a sputtering ion source for ion implantation
R. M. Allen

Ion implantation depth distributions: energy deposition into atomic processes and ion locations
D. K. Brice

Ion implantation target stage for an electromagnetic isotope separator
J. H. Freeman and G. A. Gard

A simple ion source for implantation doping of semiconductors
P. S. Gwozdz and J. S. Koehler

Electron microprobe study of ion implantation
C. Legrand, C. Bahezre, and J. Le Duigou

Method of simultaneous epitaxial growth and ion implantation
Ramzy G. Mankarious
(Hughes Aircraft Co.), U. S. Patent 3,520,741 (July 14, 1970)

Atomic Collision Phenomena in Solids
D. W. Palmer, M. W. Thompson, and P. D. Townsend, eds.
Proceedings of an International Conference held at the University of Sussex, Brighton, England, Sept. 7-12, 1969

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Investigation of ion-implanted crystals by means of directional effects in charged-particle reaction yields
E. Bogh

Semiconductor doping by "ionic implantation"
R. B. Brocard
Toute Electronique, 36(334):112-114 (1969)


Structure effects in low-energy electronic stopping (ions)
I. M. Cheshire, G. Dearnaley, and J. M. Poate

The range and energy loss of implanted ions
G. Dearnaley

Ion bombardment and implantation
G. Dearnaley
About 270 refs.

Doping solids with ions
Geoff Dearnaley and J. Harry Freeman

Doping of semiconductors and semiconducting film. Vol. II

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Channeling effect and its application to ion implantation phenomena
Lennart Eriksson

Use of isotope separators for ion implantation
J. H. Freeman

Fabricating solid state devices by ion implantation
Alfred J. Gale

Ion implantation by means of nuclear reactions
L. Grodzins

Surface ionization source for ion implantation
D. M. Jamba

Ion implantation: a new method of doping semiconductors - I.
L. N. Large

Ion implantation: a new method of doping semiconductors - II
L. N. Large

The application of ion implantation to semiconductor devices
L. N. Large and K. G. Hambleton

Slowing-down of ions (review)
J. Lindhard

Ion implantation in semiconductors
J. W. Mayer and G. J. Marsh

Physical state of ion implanted solids
R. S. Nelson

The equilibrium topography of sputtered amorphous solids
M. J. Nobes, J. S. Colligon, and G. Carter

Theory for the sputtering of amorphous solid by an ion beam and the changes in surface topography
Channeling in semiconductors and its application to the study of ion implantation
S. T. Piaurax

Channeling studies in diamond-type lattices (diamond; silicon; germanium; gallium phosphide; gallium arsenide; gallium antimonide)